

# INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)

SETI-0006

Application Number

10/659,183

Applicant(s)

Fareed et al.

Filing Date

September 10, 2003

Group Art Unit

Unknown

\*EXAMINER  
INITIAL

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

"Ferroelectric Semiconductors," V. M. Fridkin, Russia (1976), p. 90 (pp. 64-65 in English version).

"High Pinch-off Voltage AlGaIn-GaN Heterostructure Field Effect Transistor," M. S. Shur et al., Proceedings of ISDRS-97, Charlottesville, VA, December 1997, pp. 377-380.

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DATE CONSIDERED

6/13/04

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## U.S. PATENT DOCUMENTS

| *EXAMINER<br>INITIAL | REF | DOCUMENT NUMBER | DATE    | NAME            | CLASS | SUBCLASS | FILING DATE<br>IF APPROPRIATE |
|----------------------|-----|-----------------|---------|-----------------|-------|----------|-------------------------------|
| PZ                   |     | US006359292B1   | 03-2002 | Sugawara et al. |       |          |                               |
| ↓                    |     | US006316793B1   | 11-2001 | Sheppard et al. |       |          |                               |
| ↓                    |     | US005981977A    | 11-1999 | Furukawa et al. |       |          |                               |
| PZ                   |     | US005851905A    | 12-1998 | McIntosh et al. |       |          |                               |
|                      |     |                 |         |                 |       |          |                               |
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## FOREIGN PATENT DOCUMENTS

|  | REF | DOCUMENT NUMBER | DATE | COUNTRY | CLASS | SUBCLASS | Translation |    |
|--|-----|-----------------|------|---------|-------|----------|-------------|----|
|  |     |                 |      |         |       |          | YES         | NO |
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| PZ |  | "High Performance Microwave Power GaN/AlGa <sub>N</sub> MODFETs Grown By RF-Assisted MBE," N.X. Nguyen et al., Electronics Letters, Vol. 36, No. 5, 2nd March 2000, pp. 468-469.                 |

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